

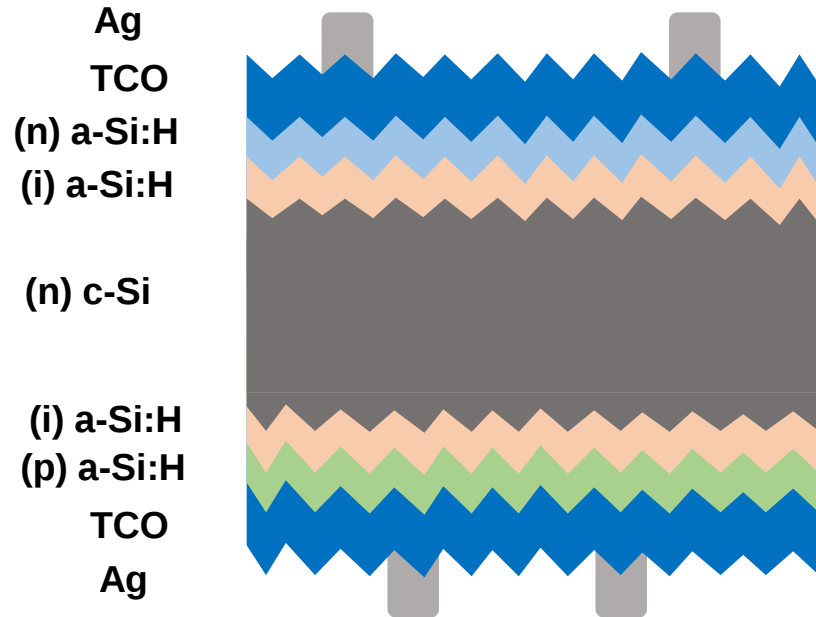


Catalytic-doping on Intrinsic Amorphous Silicon Thin Films in Silicon Heterojunction Solar Cells

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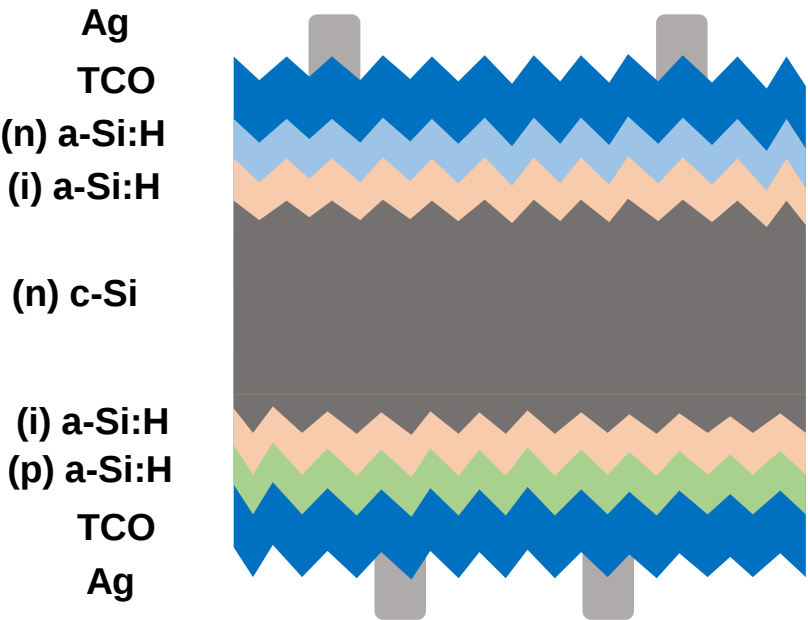
Features of SHJ Solar Cells



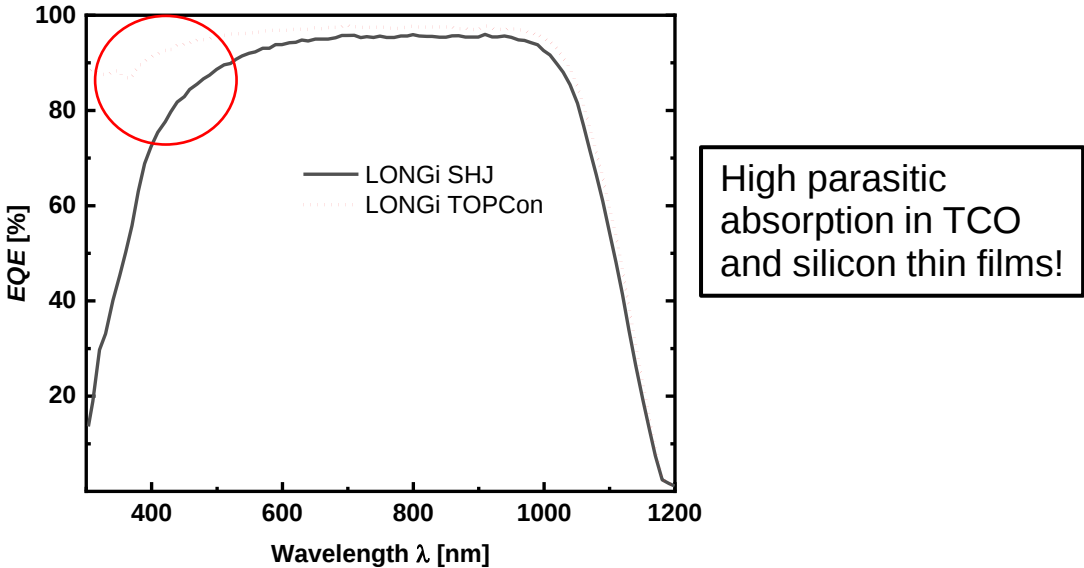
Schematic cross-section of a typical traditional silicon heterojunction (SHJ) solar cell

- High efficiency (record 26.5%).
- Mass production efficiency > 25%.
- Low thermal coefficient (< 0.3 %/°C).
- Simple processing (5 steps).
- Compatible with thinner wafers (< 100μm).
- High bifaciality (95%).
- Partner for tandem.

Efficiency Limitation of SHJ Solar Cells



Schematic cross-section of a typical traditional silicon heterojunction (SHJ) solar cell

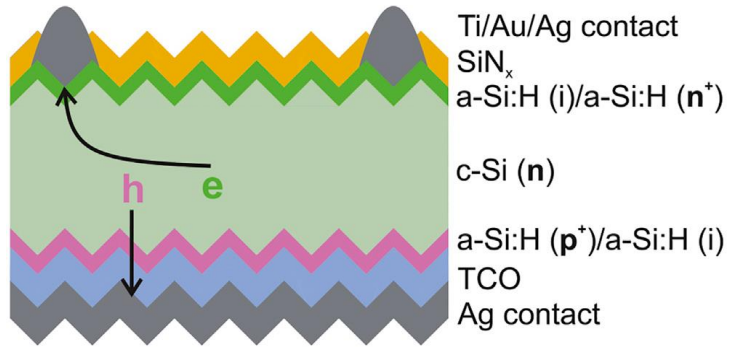


Cell type	V_{oc} [mV]	J_{sc} [mA/cm ²]	FF [%]	Eff [%]	Area [cm ²]
LONGi SHJ	748.5	39.48	85.46	25.26	244.53
LONGi TOPCon	721.6	41.64	83.90	25.21	242.97

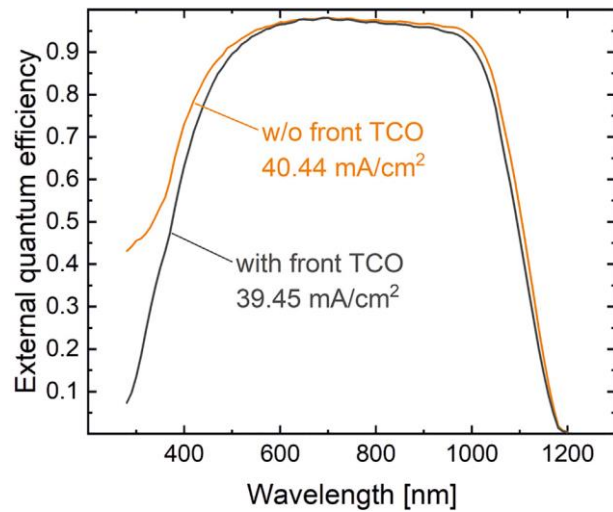
<https://taiyangnews.info/technology/longi-claims-3-new-cell-conversion-efficiency-records/>

J_{sc} Improvement of SHJ in Jülich

➤ TCO-free

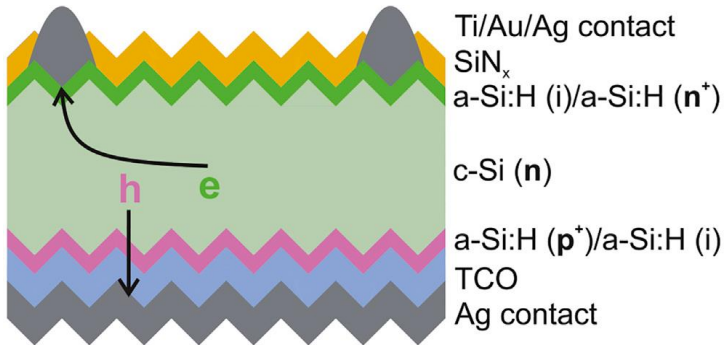


Joule 5, 2021,1535-1547

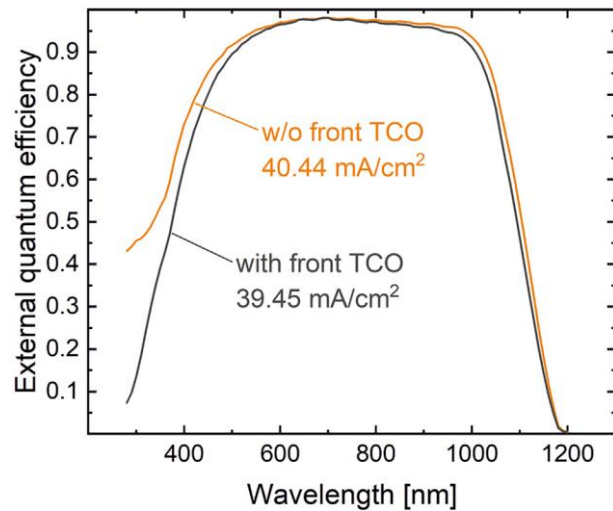


J_{sc} Improvement of SHJ in Jülich

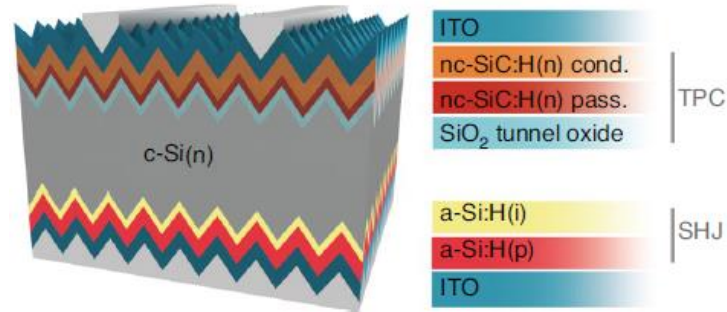
➤ TCO-free



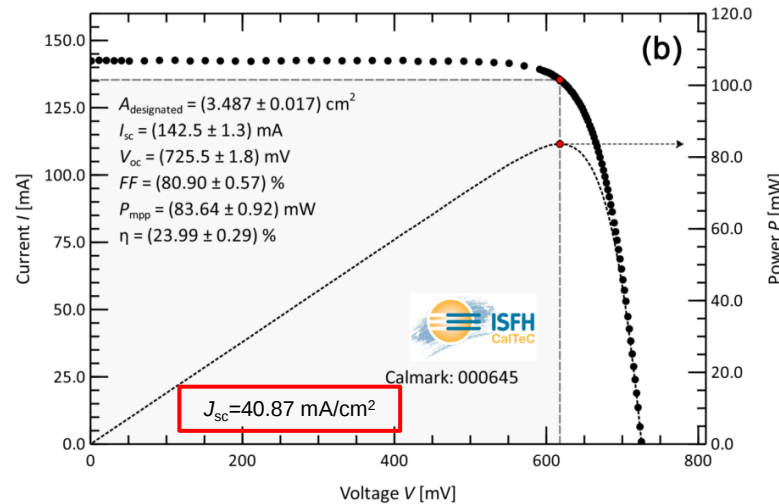
Joule 5, 2021,1535-1547



➤ Transparent passivating contact (TPC)

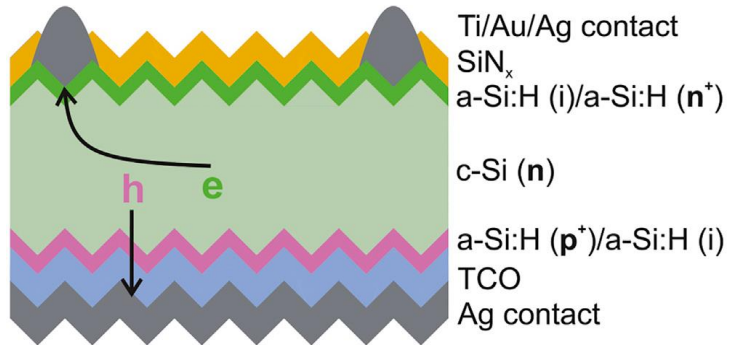


Nature Energy 6, 2021,529-537

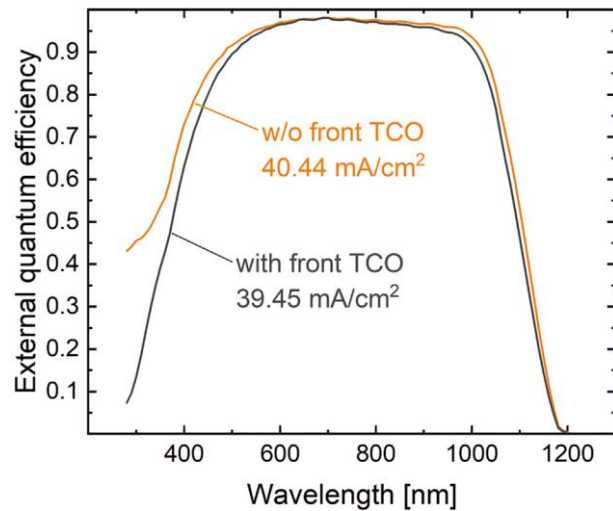


J_{sc} Improvement of SHJ in Jülich

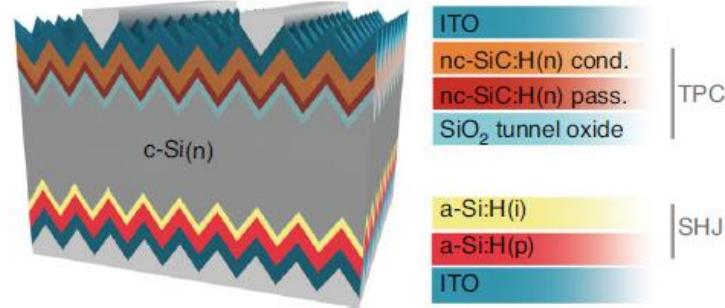
➤ TCO-free



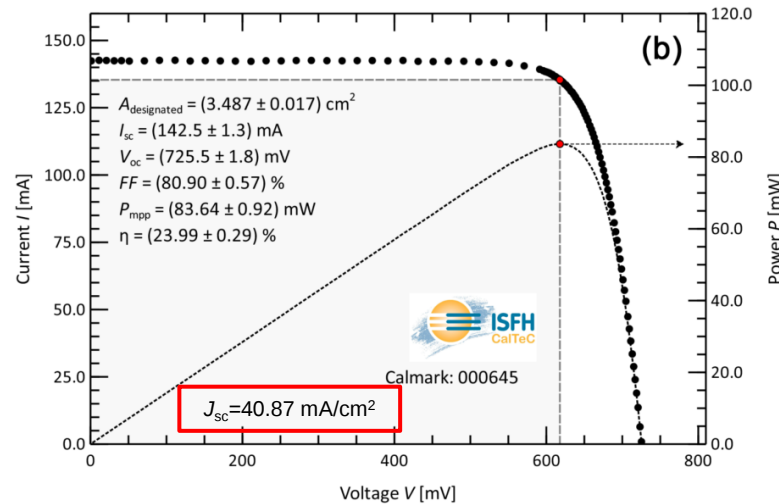
Joule 5, 2021,1535-1547



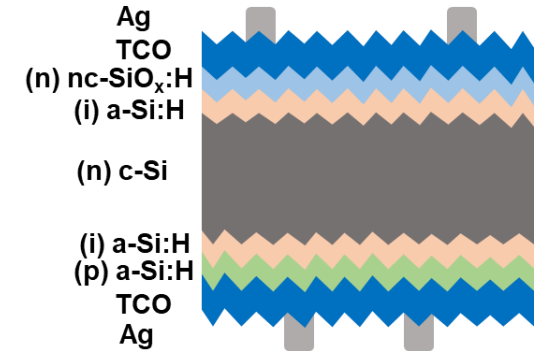
➤ Transparent passivating contact (TPC)



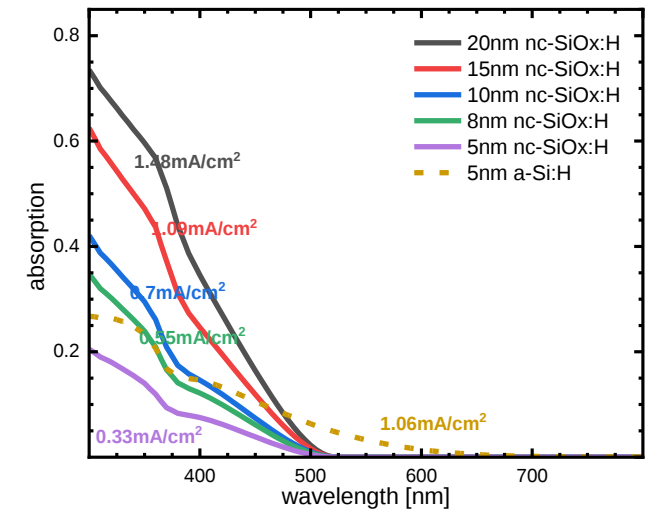
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➤ nc-SiO_x:H window layer



Solar Energy Materials & Solar Cells 209, 2020, 110471

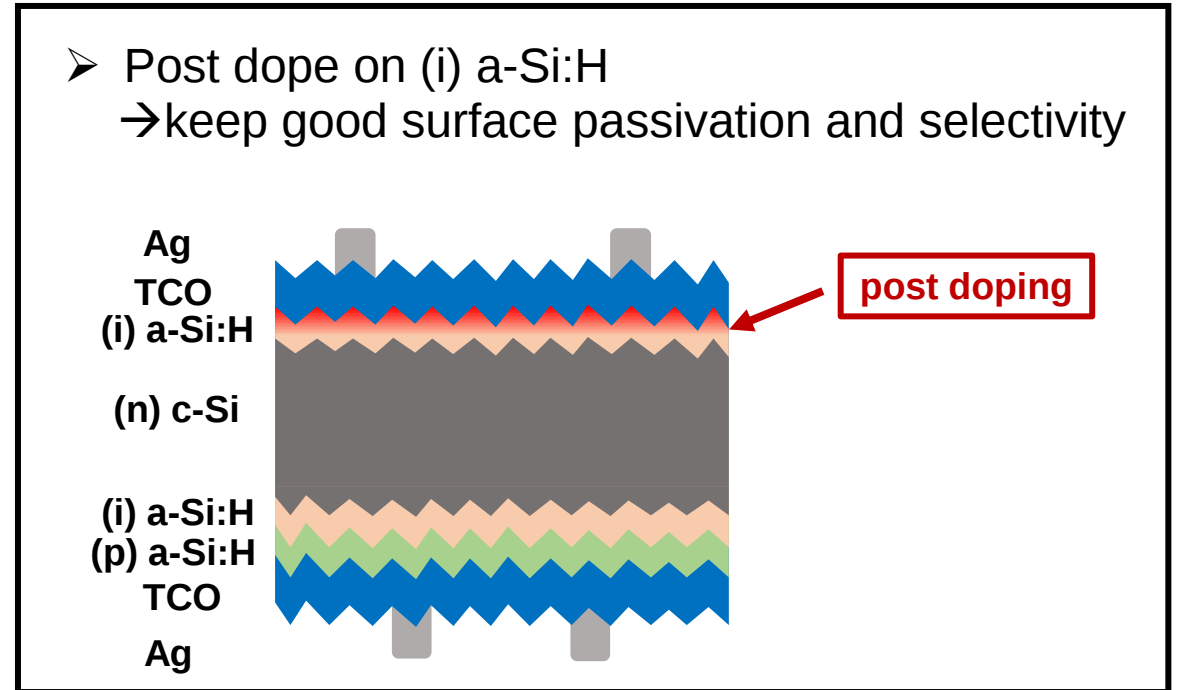


J_{sc} Improvement by Reducing Silicon Thin Film Thickness

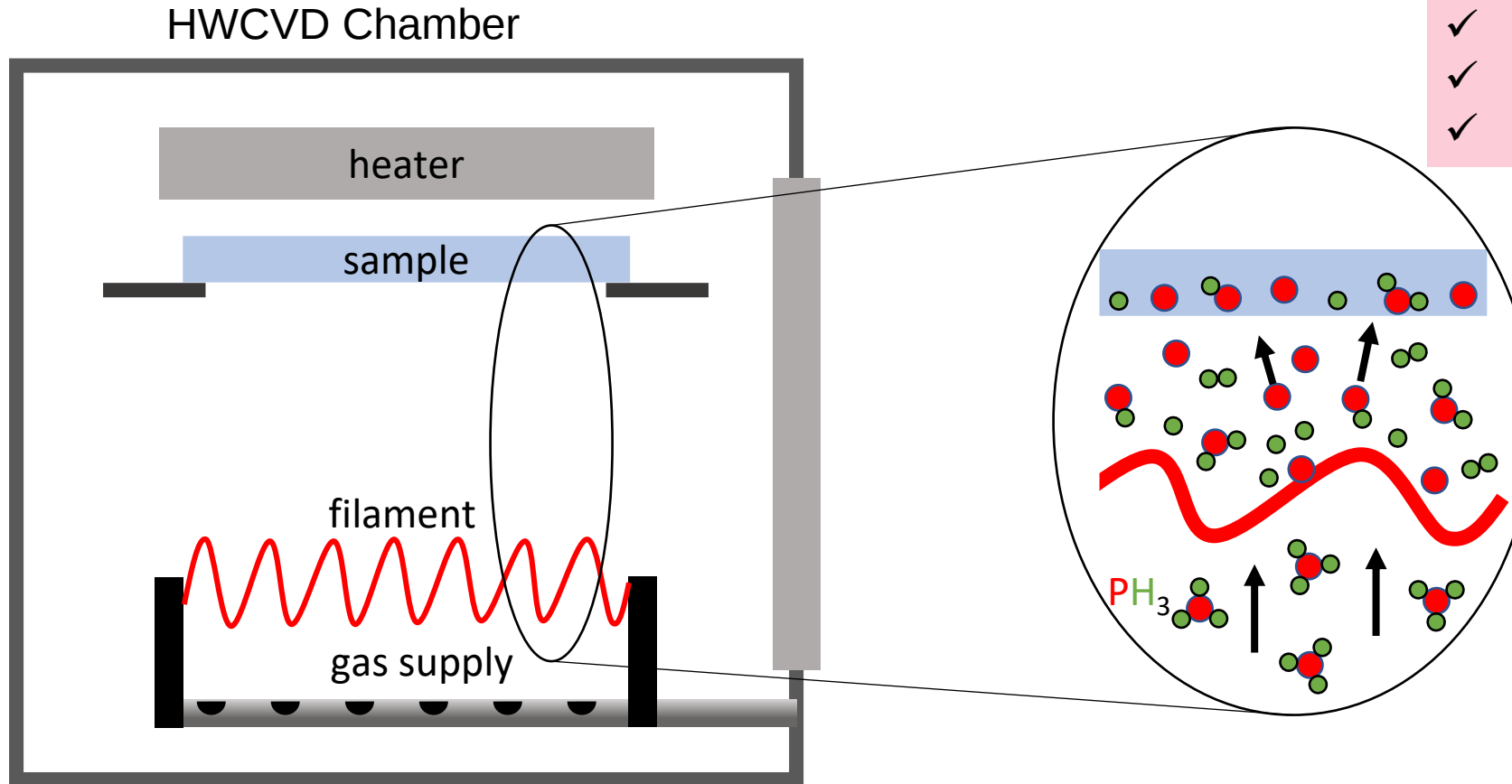
- Reduce n doped layer thickness
→ decrease selectivity
- Reduce front (i) a-Si:H thickness
→ decrease surface passivation

J_{sc} Improvement by Reducing Silicon Thin Film Thickness

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Catalytic Doping (Cat-doping)

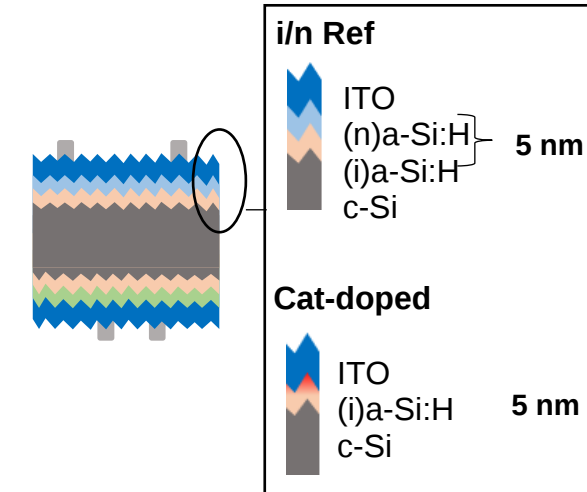
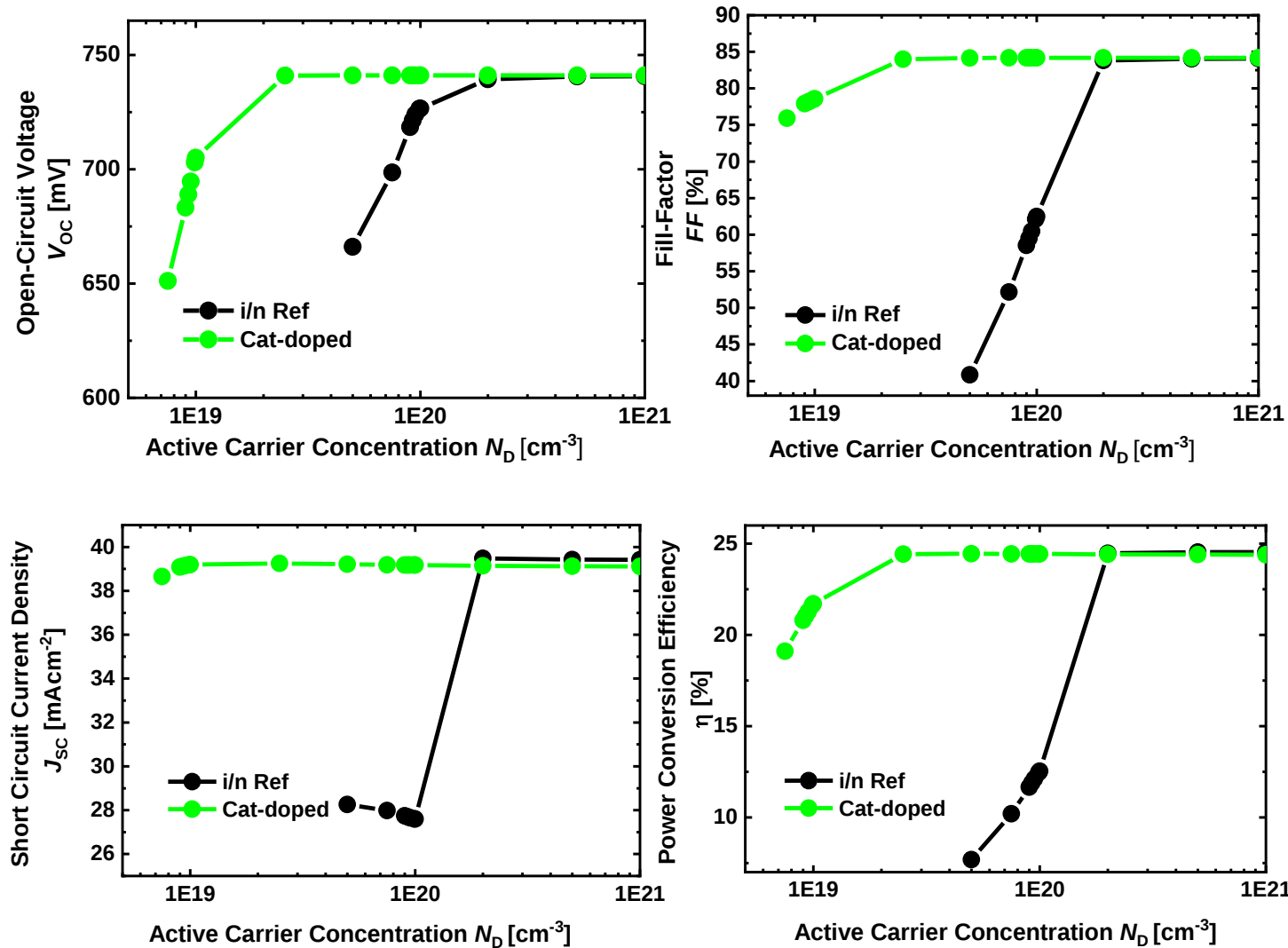


- ✓ low T_{sub} ($<200\text{ }^{\circ}\text{C}$)
- ✓ No plasma damage
- ✓ shallow doping depth
- ✓ simple, efficient, up-scalable

effects:

- thermal annealing
- hydrogenation
- Carrier doping

Proof of Concept by Simulation

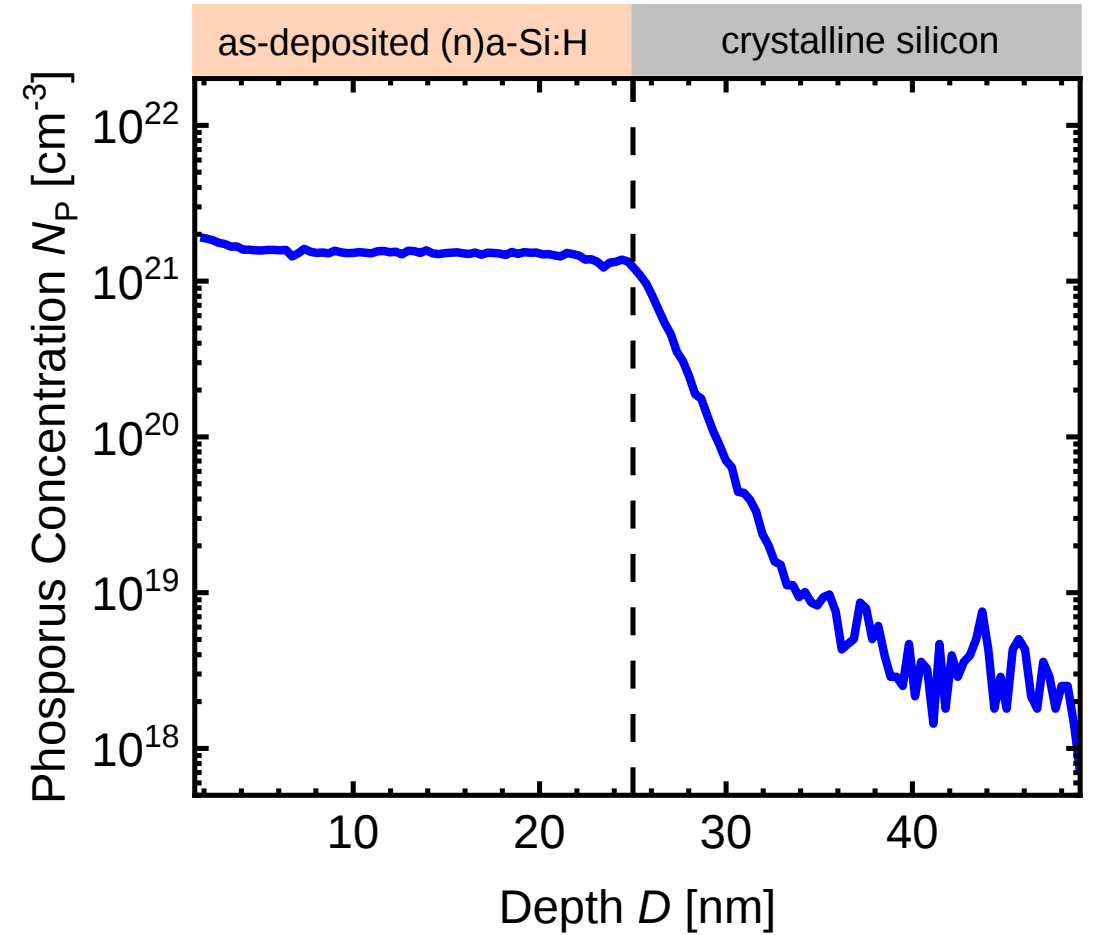
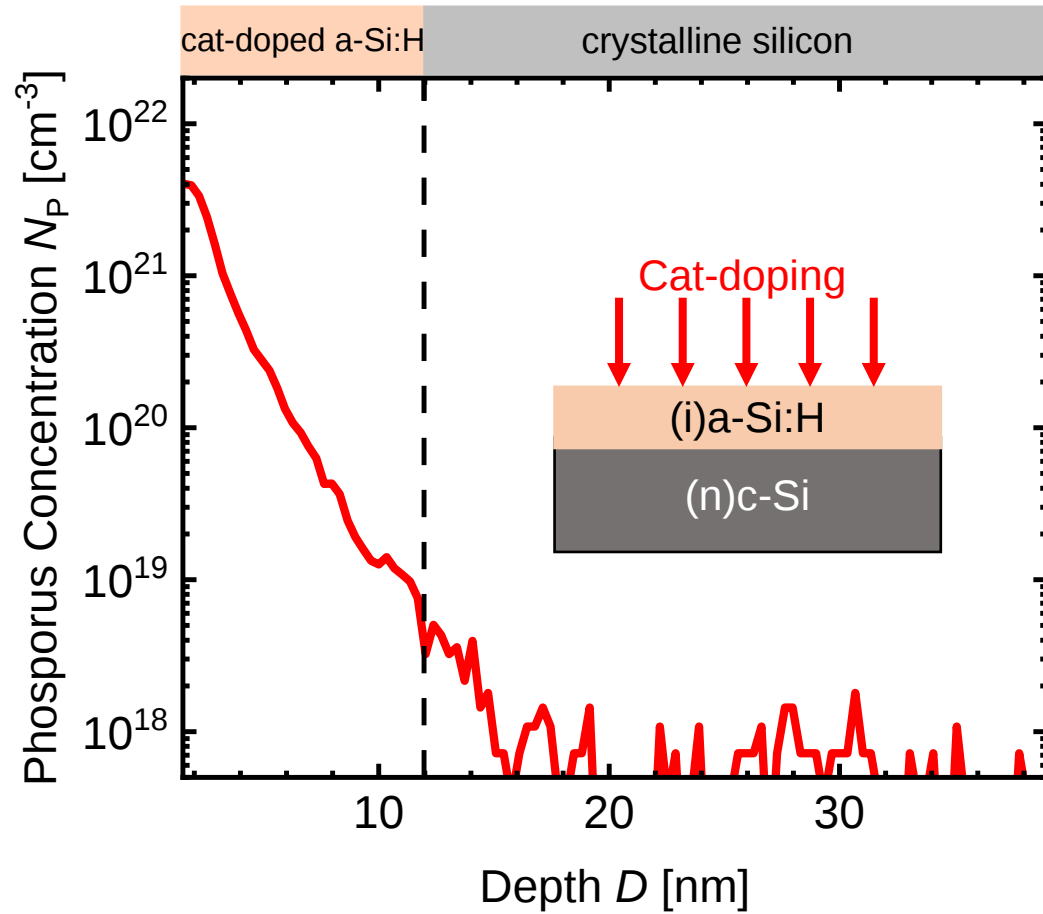


Low defects density in (i) a-Si:H

→ Less requirement of active carrier concentration for selectivity!

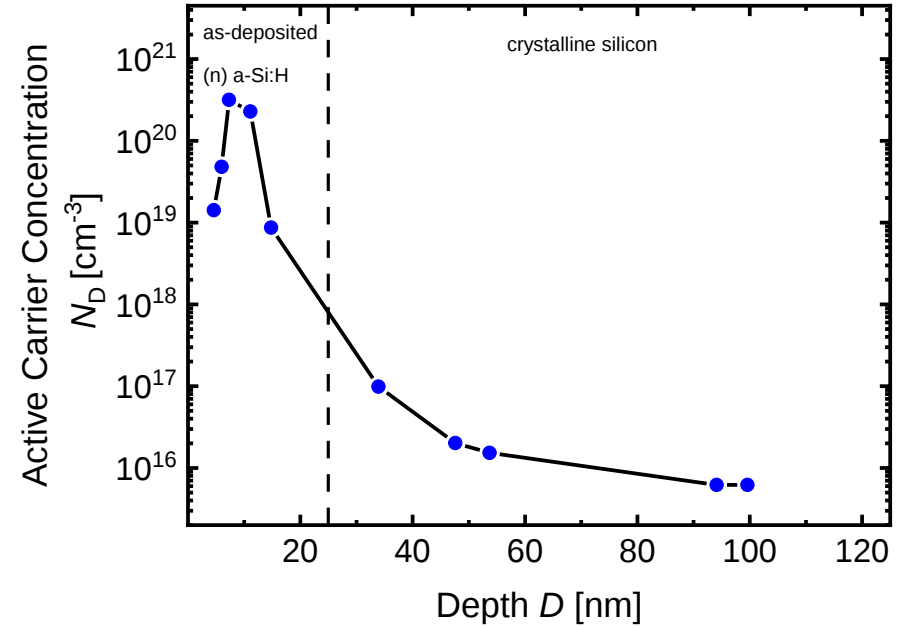
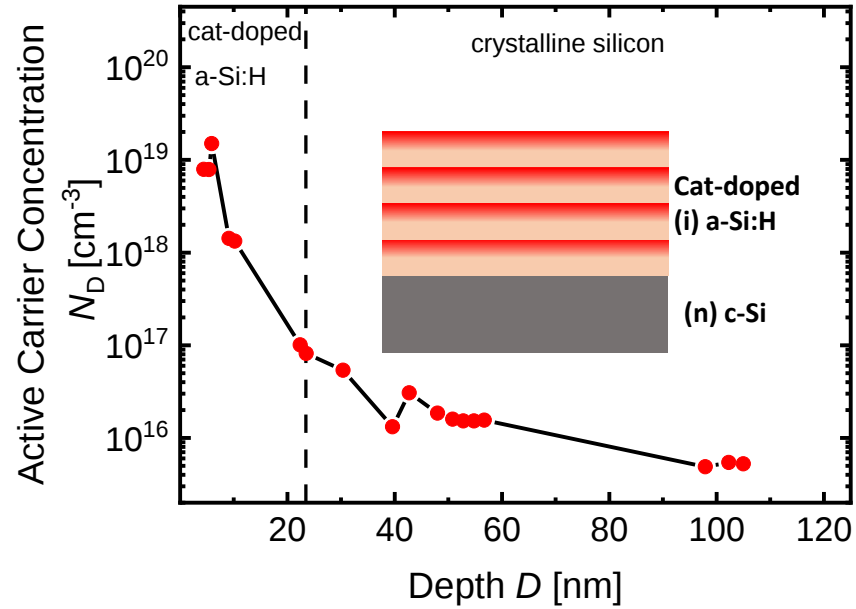
Thin Film Characterization

Secondary Ion Mass Spectrometry (SIMS) results



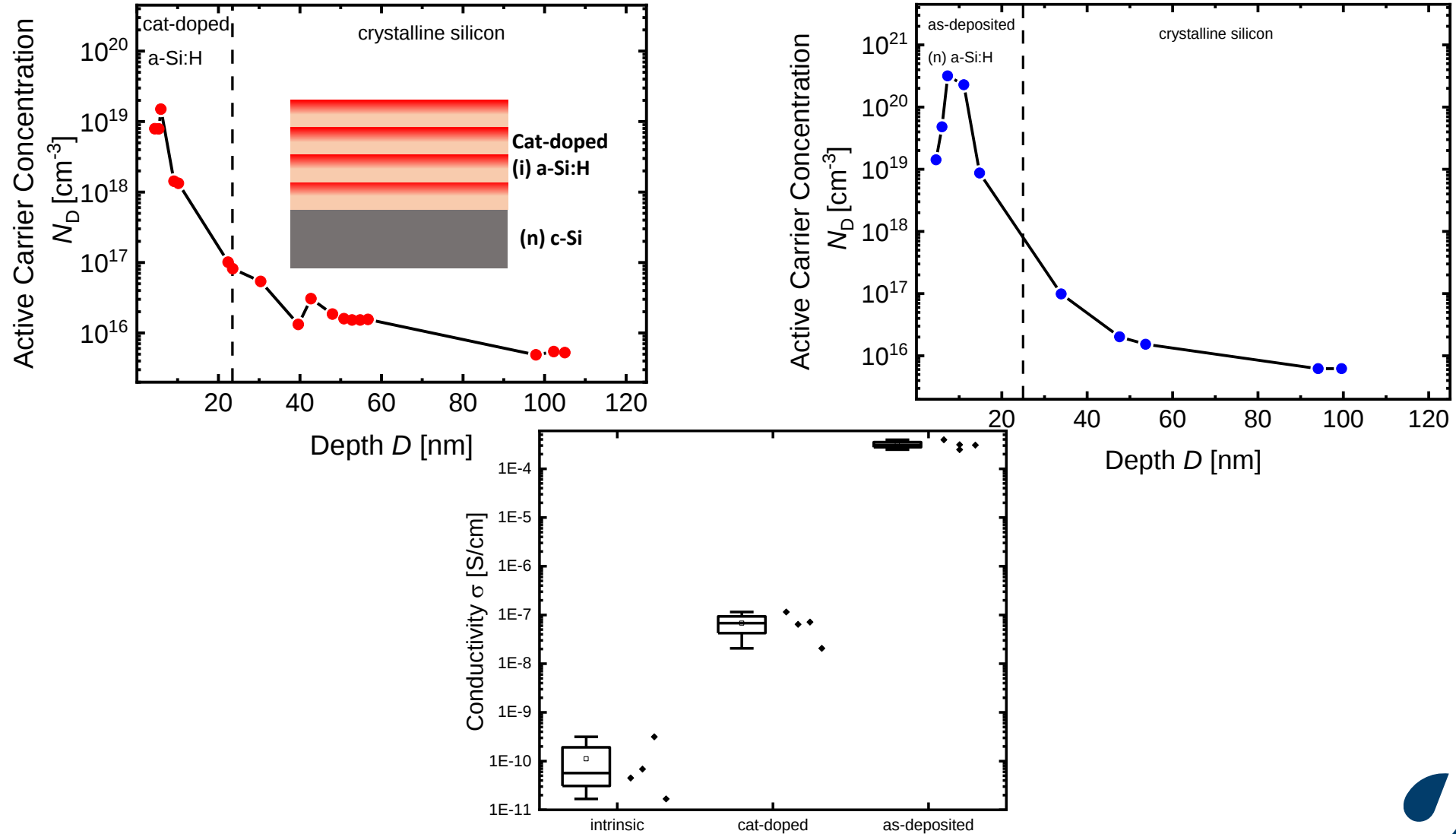
Thin Film Characterization

Electrochemical Capacitance-Voltage Measurement (eCV) and conductivity results



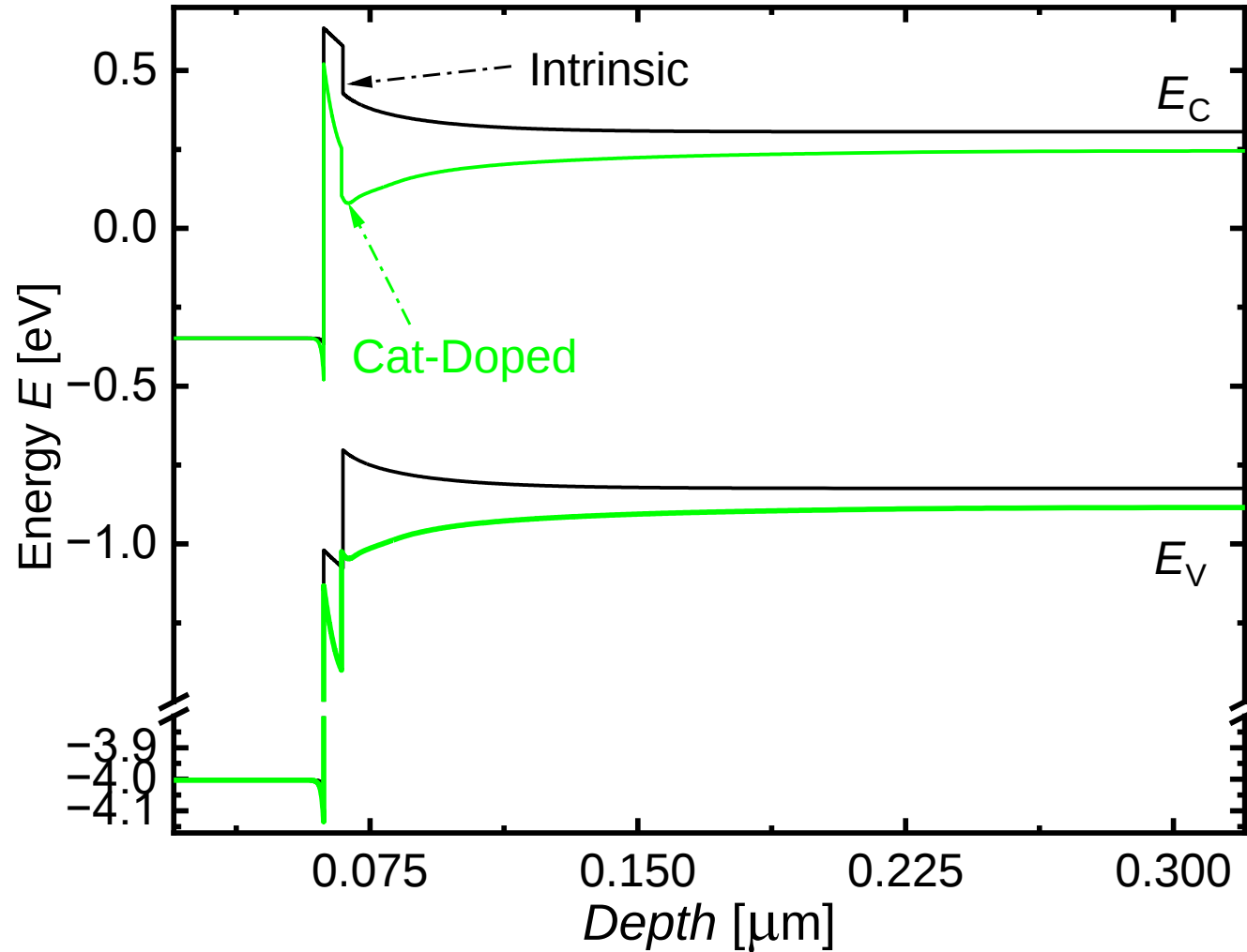
Thin Film Characterization

Electrochemical Capacitance-Voltage Measurement (eCV) and conductivity results



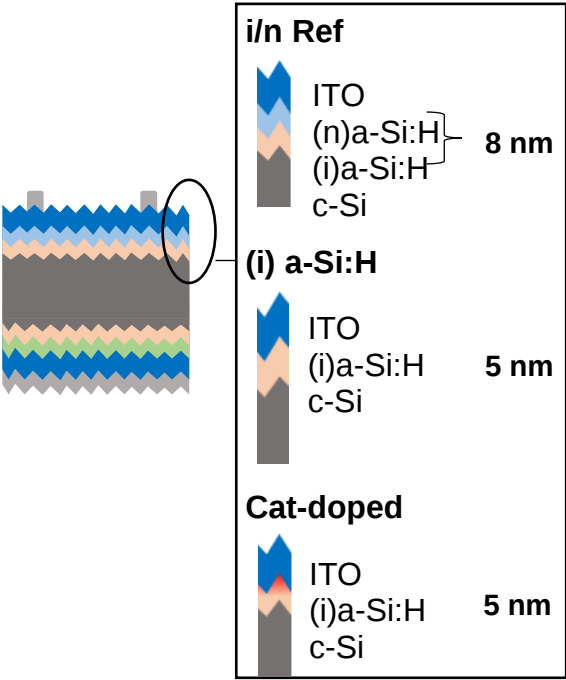
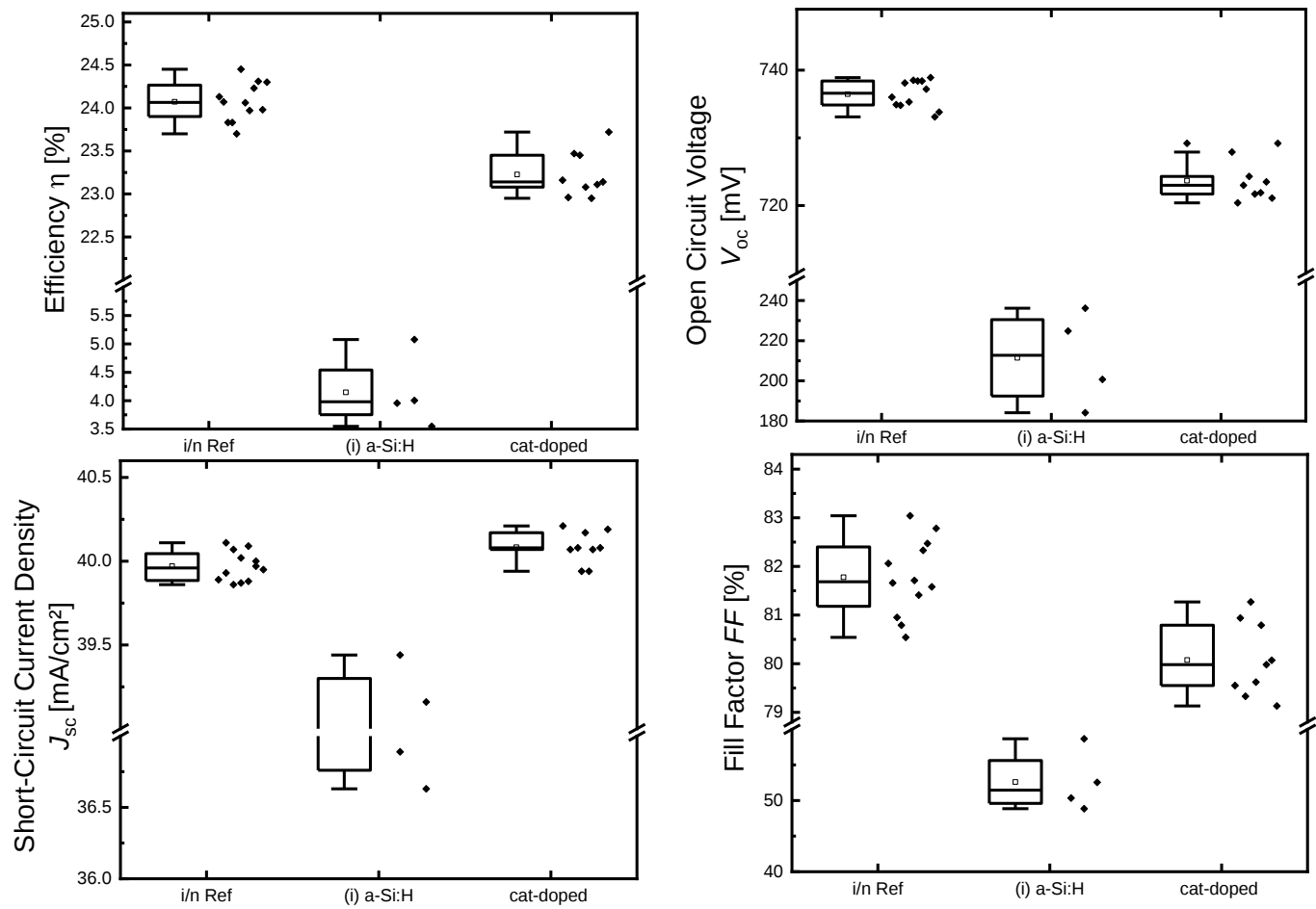
Passivation Enhancement with Cat-doping

Band diagram of (i) a-Si:H vs cat-doped (ii) a-Si:H at the same biasing voltage near MPP

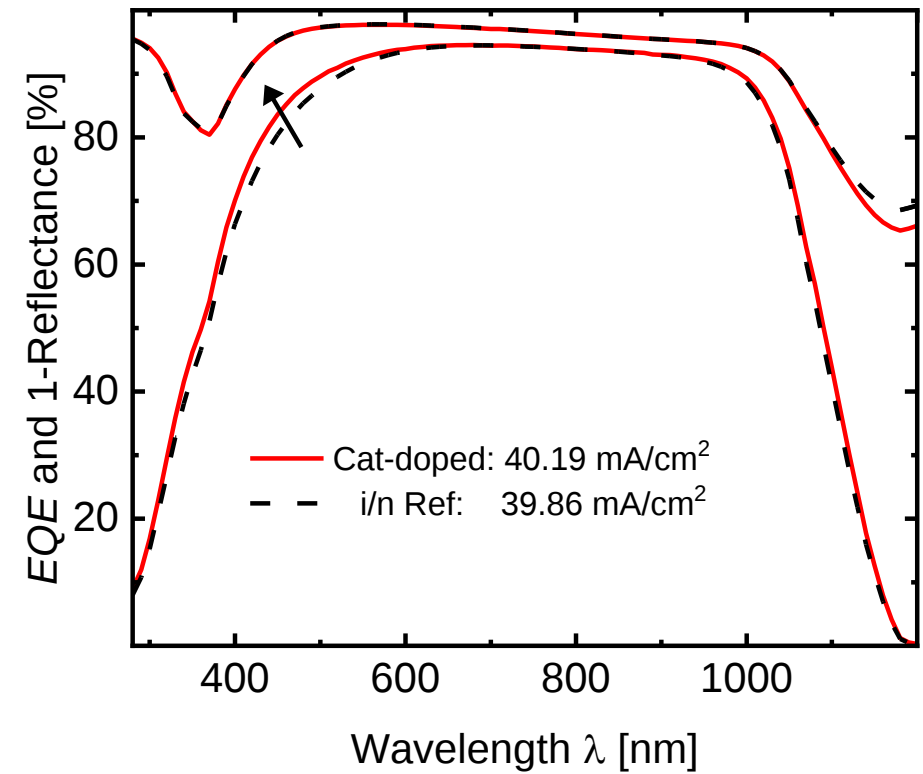
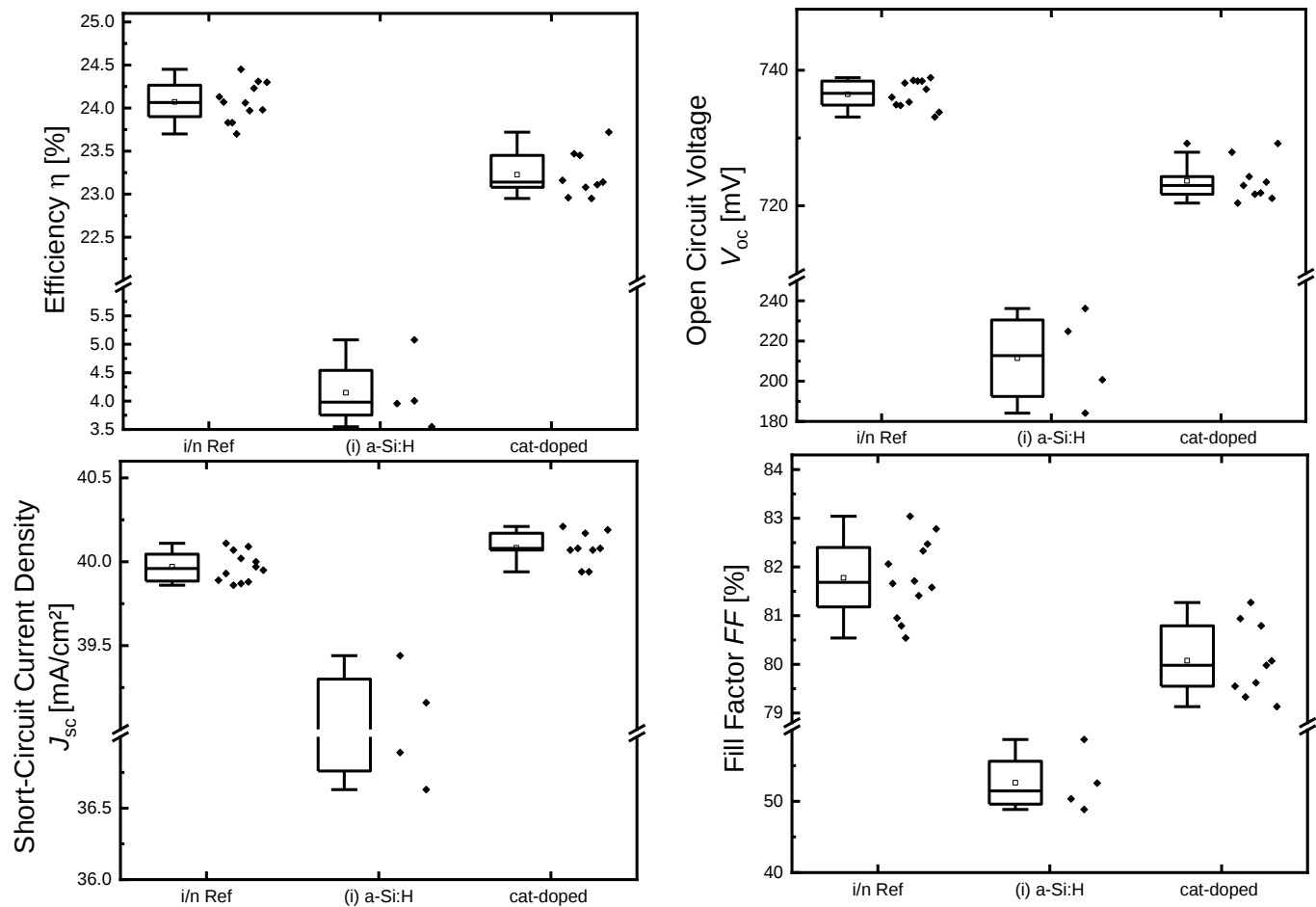


- Cat-doping can result in band bending in c-Si near the surface! It is beneficial for carrier selectivity and passivation.

Solar Cell results



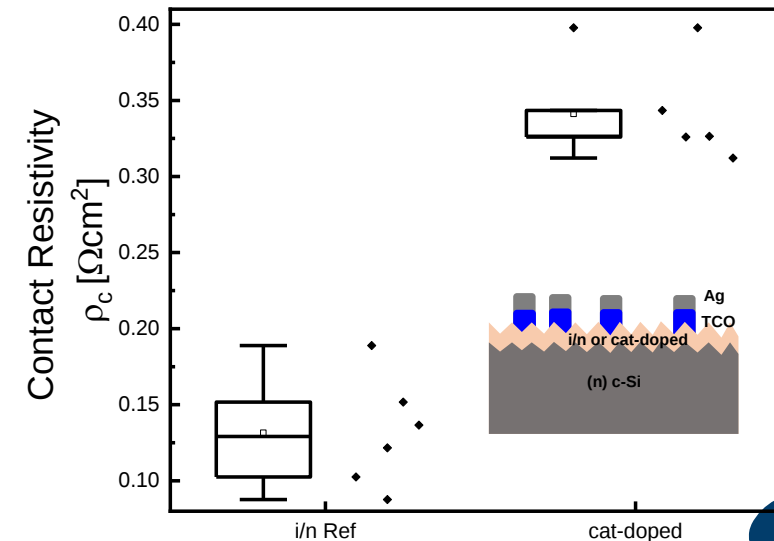
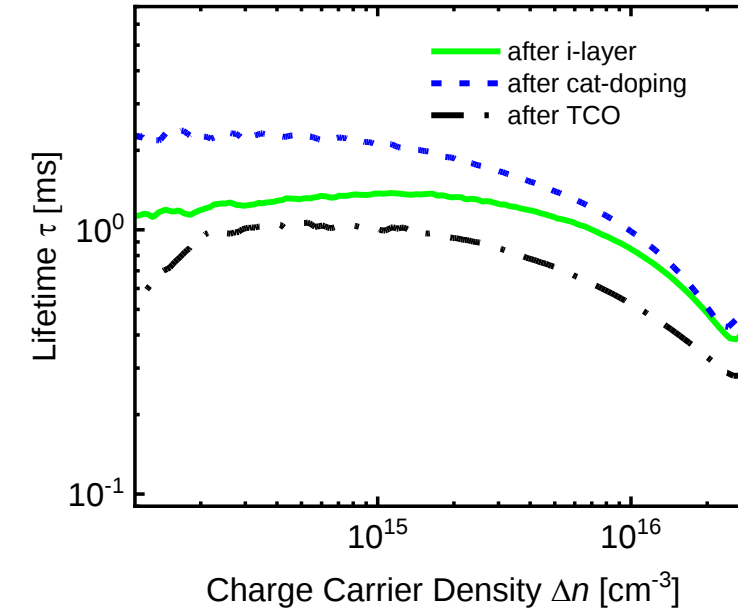
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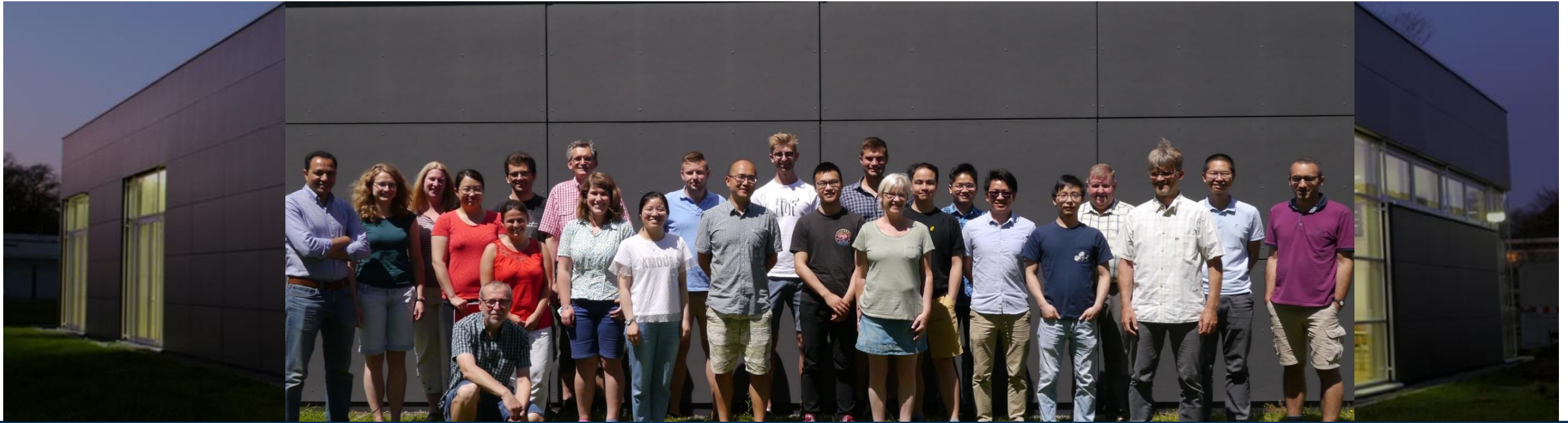


	Eff [%]	V_{oc} [mV]	J_{sc} [mA/cm ²]	FF [%]	PFF [%]
i/n Ref	24.45	738.5	39.86	83.04	83.70
Cat-doped	23.72	729.2	40.19	80.94	83.20

Directions for Further Improvement

- Reduce TCO sputter damage
 - soft TCO depositions
 - denser (i) a-Si:H
- Reduce contact resistance between TCO/cat-doped layer
 - optimization of cat-doping process
 - microstructure variation of (i) a-Si:H





THANK YOU FOR YOUR ATTENTION

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